DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

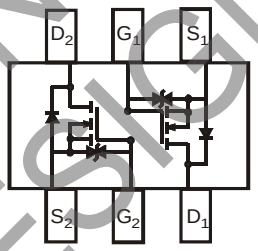
- Dual N-Channel MOSFET
- Low On-Resistance (1.0V Max)
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **ESD Protected up to 2kV**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.006 grams (Approximate)

SOT363

Top View



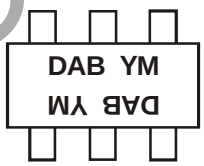
Top View
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN5L06DWK-7	SOT363	3,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



DAB = Marking Code
YM = Date Code Marking
Y = Year ex: G = 2019
M = Month ex: 9 = September

Date Code Key

Year	2006	2007	2008	…	2012	2013	2014	2015	2016	2017	2018	2019
Code	T	U	V	…	Z	A	B	C	D	E	F	G

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	50	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current Continuous Pulsed (Note 6)	I_D	305 800	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	250	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	500	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	50	—	—	V	V_{GS} = 0V, I_D = 10µA
Zero Gate Voltage Drain Current @ T_C = +25°C	I_{DSS}	—	—	60	nA	V_{DS} = 50V, V_{GS} = 0V
Gate-Body Leakage	I_{GSS}	—	—	1 500 50	µA nA nA	V_{GS} = ±12V, V_{DS} = 0V V_{GS} = ±10V, V_{DS} = 0V V_{GS} = ±5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.49	—	1.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	— — —	— — —	3.0 2.5 2.0	Ω	V_{GS} = 1.8V, I_D = 50mA V_{GS} = 2.5V, I_D = 50mA V_{GS} = 5.0V, I_D = 50mA
On-State Drain Current	$I_{D(ON)}$	0.5	1.4	—	A	V_{GS} = 10V, V_{DS} = 7.5V
Forward Transconductance	$\|Y_{FS}\|$	200	—	—	mS	V_{DS} = 10V, I_D = 0.2A
Source-Drain Diode Forward Voltage	V_{SD}	0.5	—	1.4	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	—	50	pF	V_{DS} = 25V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	—	5.0	pF	
Gate Resistance	R_G	—	65	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_G	—	0.4	—	nC	V_{GS} = 4.5V, V_{DS} = 10V, I_D = 0.25A
Gate-Source Charge	Q_{GS}	—	0.1	—	nC	
Gate-Drain Charge	Q_{GD}	—	0.1	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	2.1	—	ns	V_{DD} = 30V, V_{GS} = 10V, R_G = 25Ω, I_D = 0.2A
Turn-On Rise Time	t_R	—	1.8	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	14.4	—	ns	
Turn-Off Fall Time	t_F	—	8.4	—	ns	

Notes: 5. Device mounted on FR-4 PCB.
6. Pulse width ≤10µS, Duty Cycle ≤1%.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

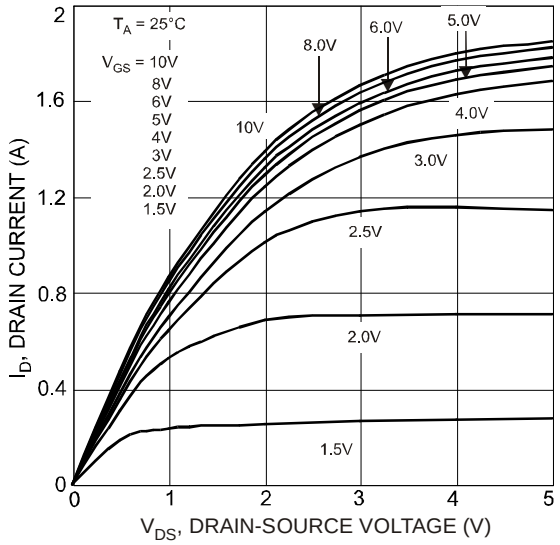


Fig. 1 Typical Output Characteristics

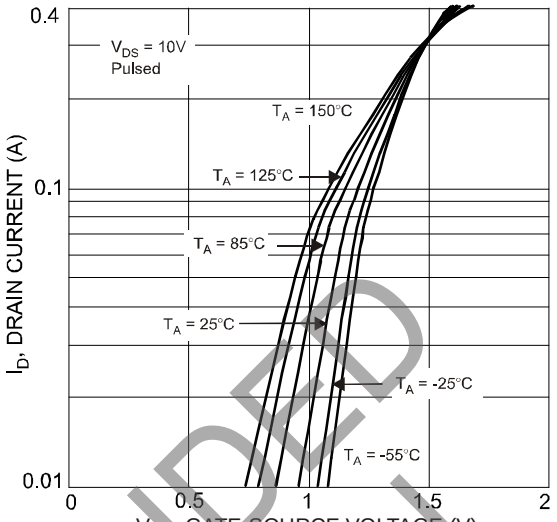


Fig. 2 Typical Transfer Characteristics

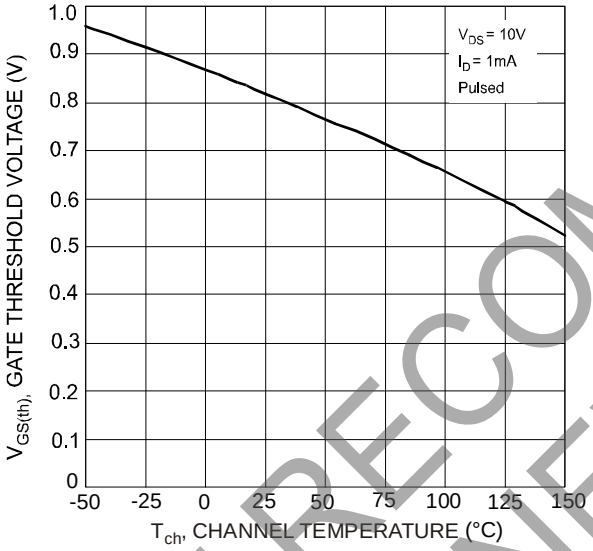


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

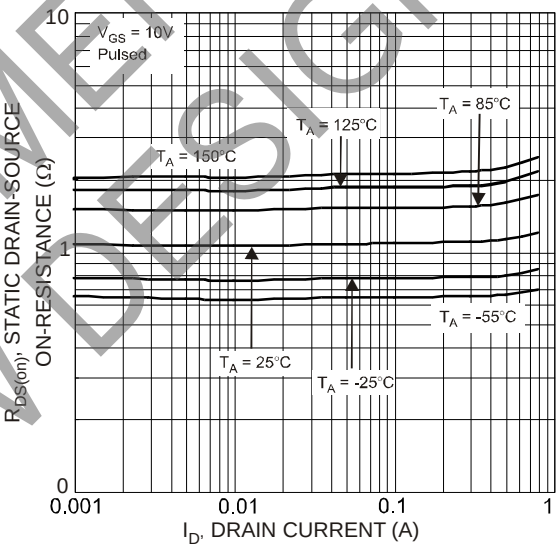


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

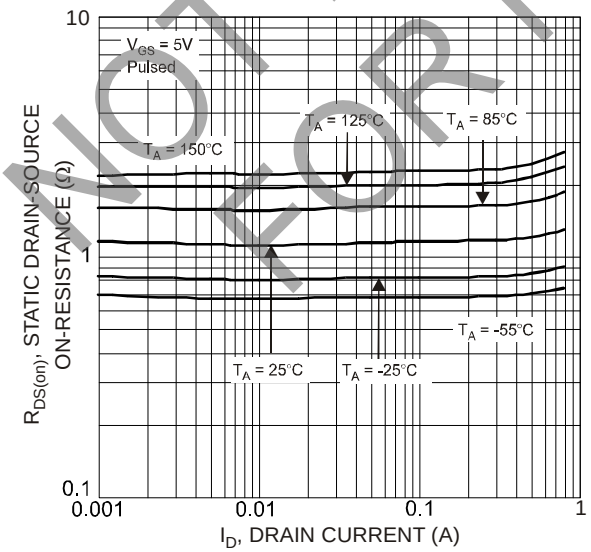


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

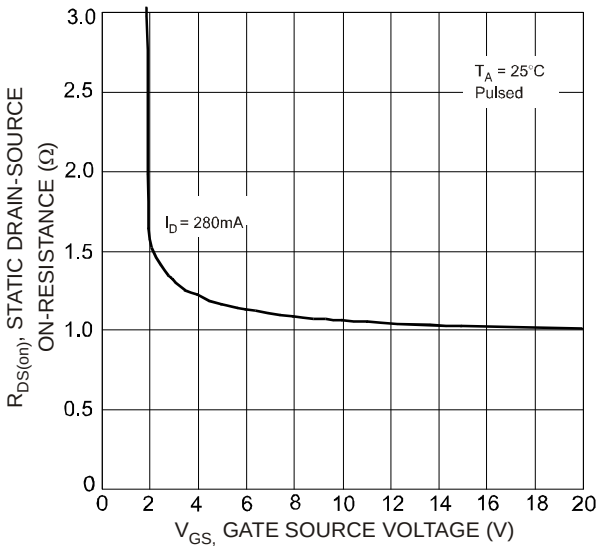


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

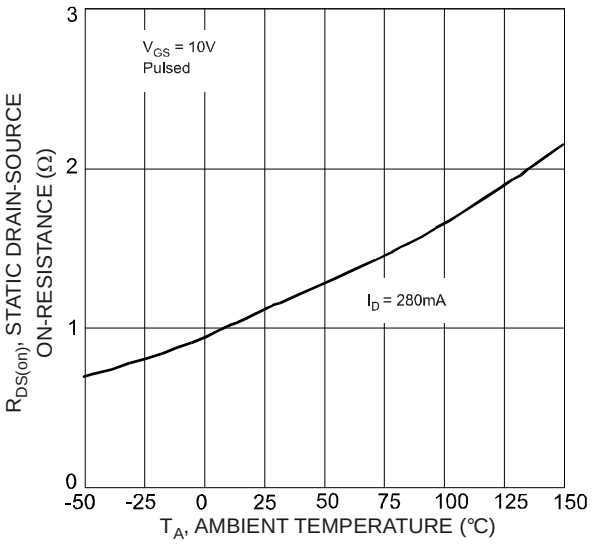


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

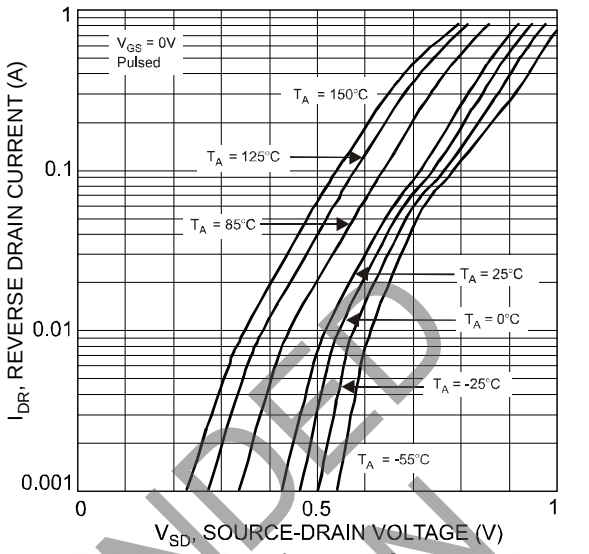


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

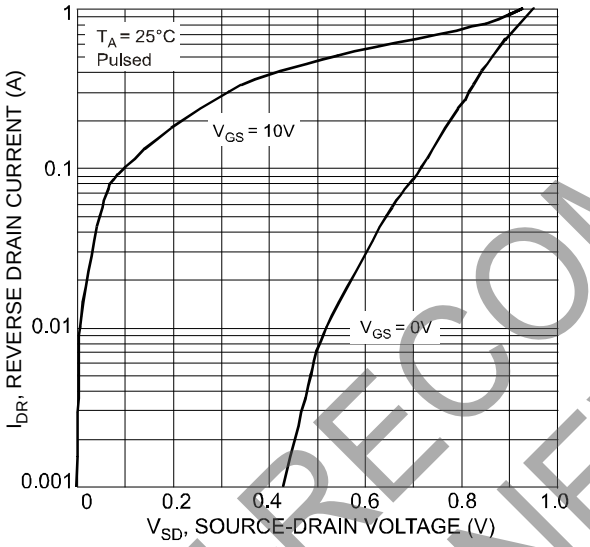


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

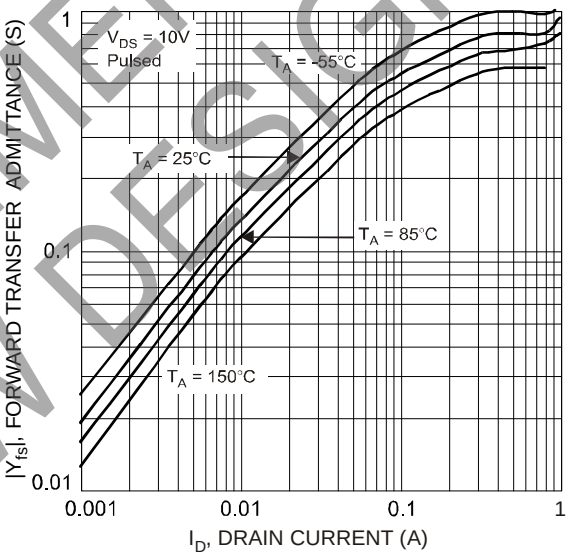


Fig.10 Forward Transfer Admittance vs. Drain Current

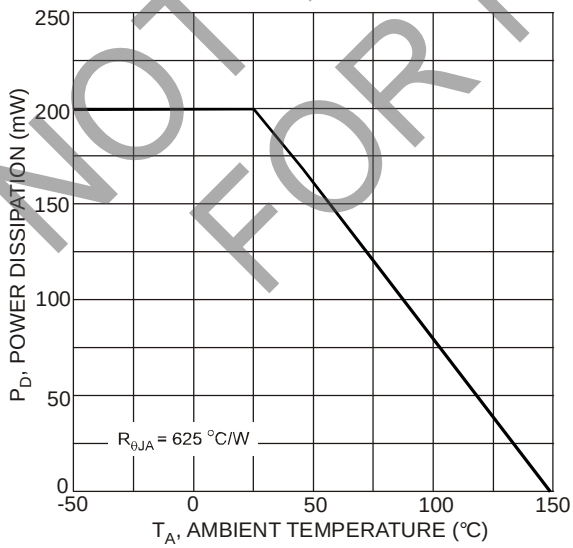


Fig. 11 Derating Curve - Total

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

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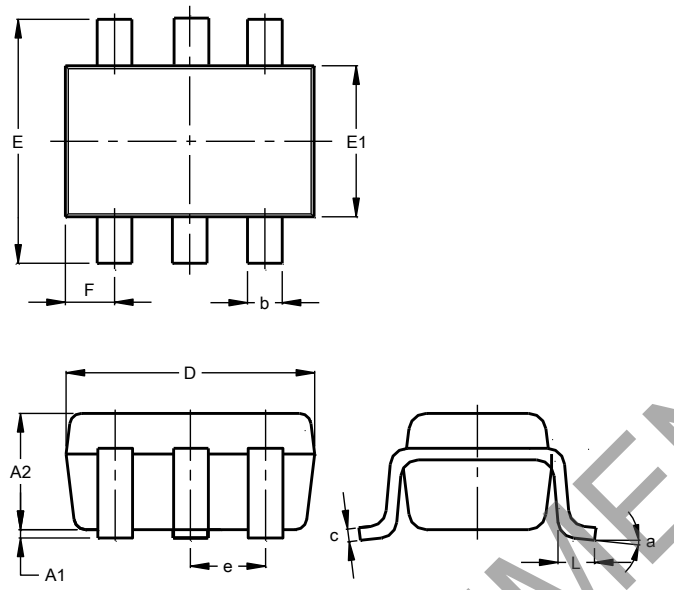

SOT363			
Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

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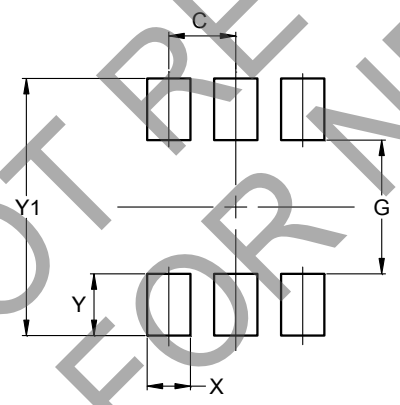

Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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